

DBF60

Silicon Diffused Junction Type

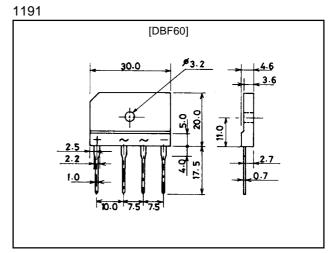
6.0A Single-Phase Bridge Rectifier

Features

- · Glass passivation for high reliability.
- · Plastic molded structure.
- · Peak reverse voltage: V_{RM} =200, 600V.
- · Average rectified current: $I_0 = 6.0 A$.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at $Ta = 25^{\circ}C$

Parameter	Symbol	Conditions	DBF60C	DBF60G	Unit
Peak Reverse Voltage	V _{RM}		200	600	V
Average Rectified Current	IO	Tc=110°C, with 125×125×1.5mm ³ AI fin	\rightarrow	6	A
		Ta=25°C, without fin	\rightarrow	2.8	A
Surge Forward Current	IFSM	50Hz sine wave, 1 cycle	\rightarrow	120	A
Junction Temperature	Tj		\rightarrow	150	°C
Storage Temperature	Tstg		\rightarrow	-40 to +150	°C

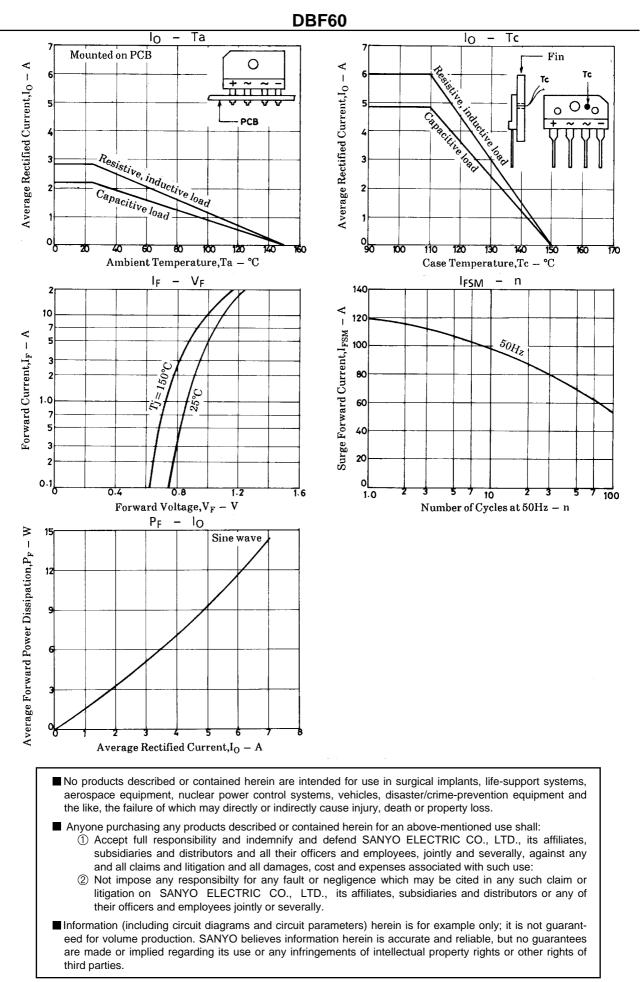
Electrical Characteristics at Ta = 25°C, per constituent element of bridge.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Forward Voltage	VF	I _F =2.5A			1.05	V
Reverse Current	IR	V _R :At each V _{RM}			10	μA
Thermal Resistance (Junction-Ambient)	Rth(j-a)	Without fin			26	°C/W
Thermal Resistance (Junction-Case)	Rth(j-c)	With AI fin			3.4	°C/W

Electrical Connection



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This catalog provides information as of May, 1998. Specifications and information herein are subject to change without notice.